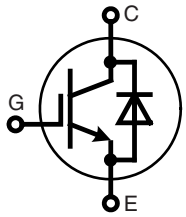
High Voltage IGBT with optional Diode ISOPLUS™ package

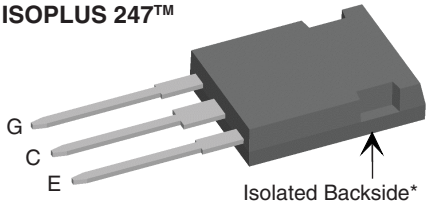
(Electrically Isolated Back Side)

V_{CES} = 1200 V
I_{C25} = 50 A
$V_{CE(sat)\ typ}$ = 2.4 V

Short Circuit SOA Capability
Square RBSOA



ISOPLUS 247™



E72873

G = Gate C = Collector E = Emitter

Symbol	Conditions		Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C		1200	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 20 kΩ		1200	V
V_{GES}	Continuous		±20	V
V_{GEM}	Transient		±30	V
I_{C25}	T_C = 25°C		50	A
I_{C90}	T_C = 90°C		30	A
I_{CM}	T_C = 90°C, t_p = 1 ms		60	A
RBSOA	V_{GE} = ±15 V, T_J = 125°C, R_G = 47 Ω		I_{CM} = 50	A
	Clamped inductive load, L = 30 mH		$V_{CEK} < V_{CES}$	
t_{SC} (SCSOA)	V_{GE} = ±15 V, V_{CE} = V_{CES}, T_J = 125°C R_G = 47 Ω, non repetitive		10	µs
P_C	T_C = 25°C	IGBT	200	W
		Diode	95	W
T_J			-55 ... +150	°C
T_{stg}			-55 ... +150	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq$ 1 mA		2500	V~
Weight			6	g

Symbol	Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{(BR)CES}$	V_{GE} = 0 V	1200			V
$V_{GE(th)}$	I_C = 1 mA, V_{CE} = V_{GE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}, T_J = 25°C			1.5	mA
	T_J = 125°C		2.5		mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V			± 500	nA
$V_{CE(sat)}$	I_C = 30 A, V_{GE} = 15 V		2.4	2.9	V

Features

- NPT IGBT technology
  - high switching speed
  - low switching losses
  - square RBSOA, no latch up
  - high short circuit capability
  - positive temperature coefficient for easy paralleling
  - MOS input, voltage controlled
  - fast recovery epitaxial diode
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Advantages

- DCB Isolated mounting tab meets TO-247AD package outline
- Package for clip or spring mounting
- Space savings
- High power density

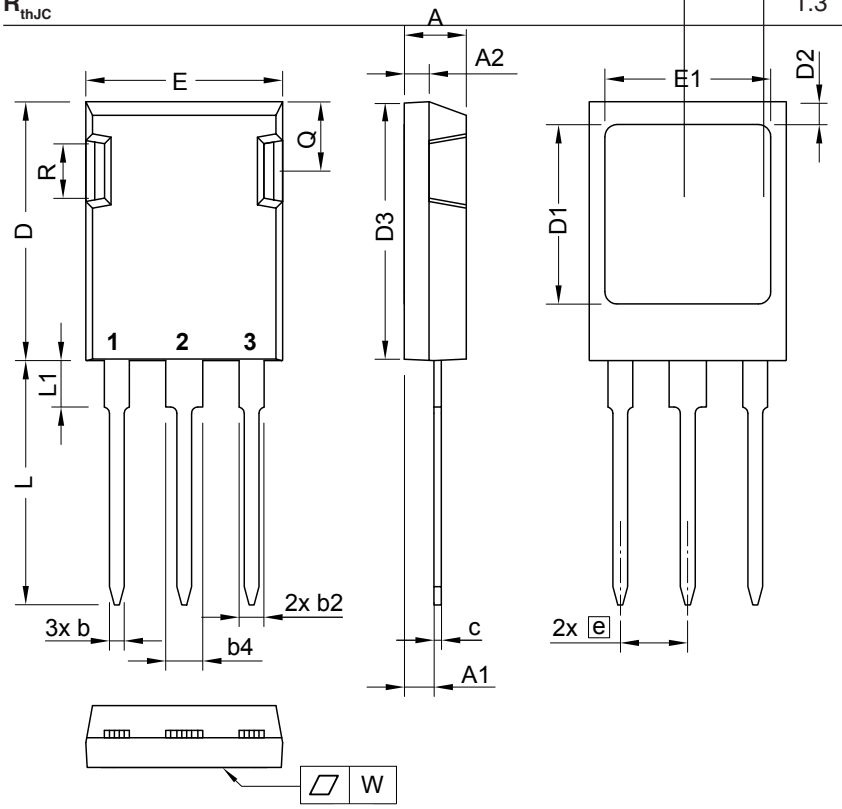
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninteruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1650		pF
C_{oes}			250		pF
C_{res}			110		pF
Q_g	I_C = 30 A, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		120		nC
$t_{d(on)}$			100		ns
t_r			70		ns
$t_{d(off)}$	**Inductive load, T_J = 125°C**		500		ns
t_f	I_C = 30 A, V_{GE} = ±15 V,		70		ns
E_{on}	V_{CE} = 600 V, R_G = 47 Ω		4.6		mJ
E_{off}			3.4		mJ
R_{thJC}				0.6	K/W
R_{thCH}	Package with heatsink compound		0.25		K/W

Reverse Diode (FRED)

Symbol	Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	I_F = 30 A, V_{GE} = 0 V		2.5	2.75	V
	I_F = 30 A, V_{GE} = 0 V, T_J = 125°C		2.0		V
I_F	T_C = 25°C			50	A
	T_C = 90°C			27	A
I_{RM}	I_F = 30 A, -di_F/dt = 400 A/µs, V_R = 600 V		20		A
t_{rr}	V_{GE} = 0 V, T_J = 125°C		200		ns
t_{rr}	I_F = 1 A, -di_F/dt = 100 A/µs, V_R = 30 V, V_{GE} = 0 V		40		ns
R_{thJC}				1.3	K/W



Dim.	Millimeter min	Millimeter max	Inches min	Inches max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	5.45 BSC		0.215 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und $L_{max.}$
This drawing will meet all dimensions requiarement of JEDEC outline TO-247 AD except screw hole and except $L_{max.}$

IXYS reserves the right to change limits, test conditions and dimensions.

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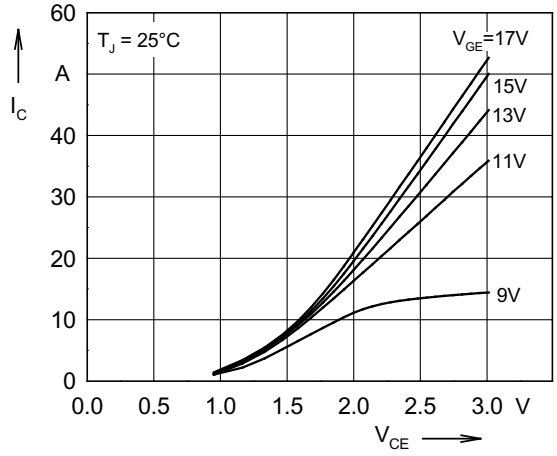

Fig. 1 Typ. output characteristics

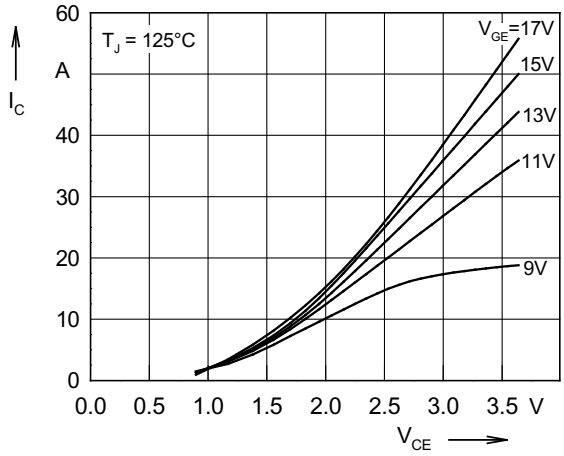

Fig. 2 Typ. output characteristics

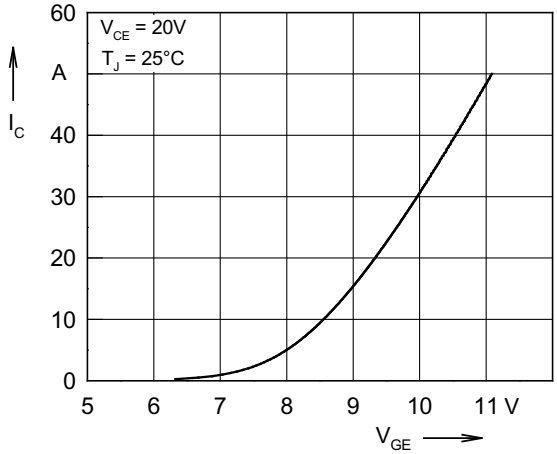

Fig. 3 Typ. transfer characteristics

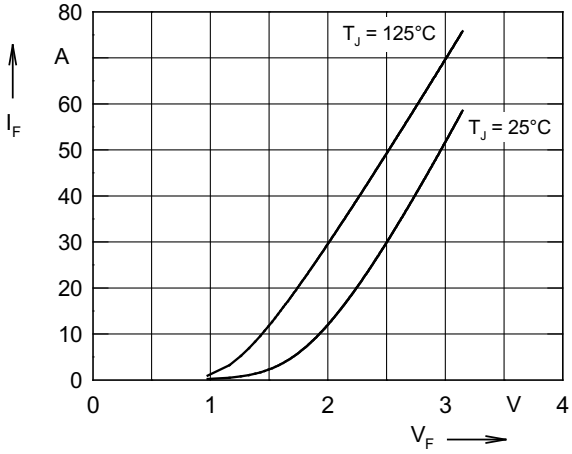

Fig. 4 Typ. forward characteristics of free wheeling diode

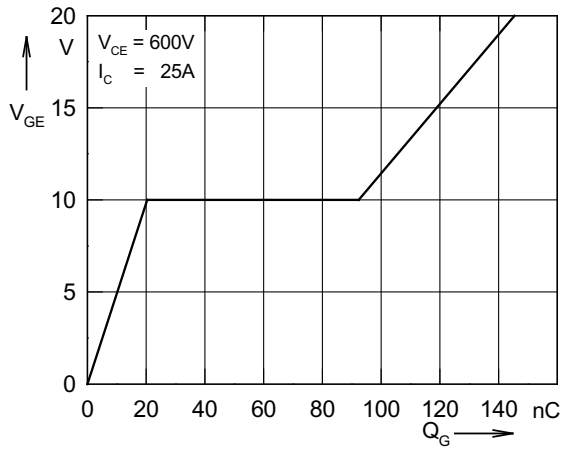

Fig. 5 Typ. turn on gate charge

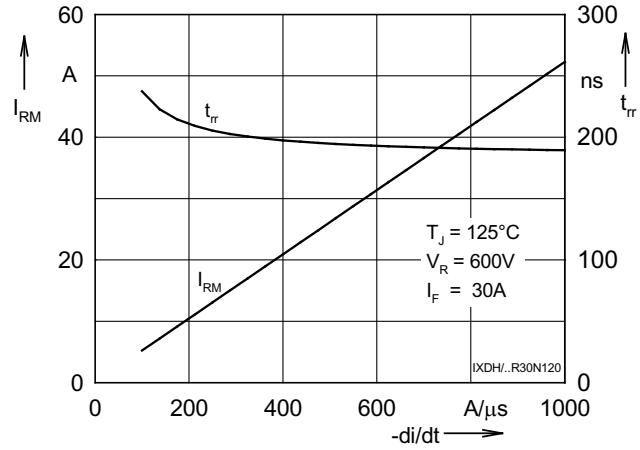

Fig. 6 Typ. turn off characteristics of free wheeling diode

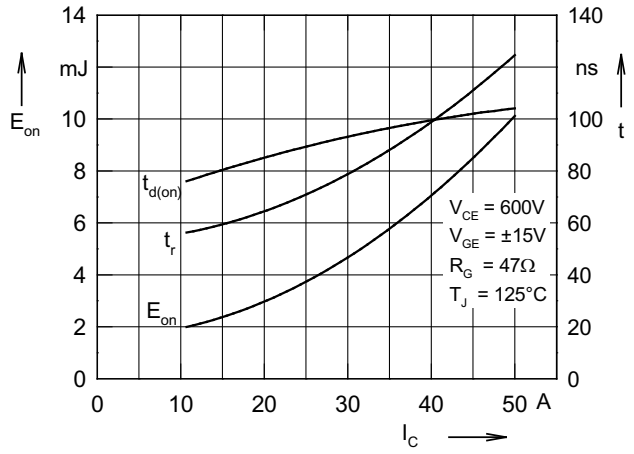

Fig. 7 Typ. turn on energy and switching times versus collector current

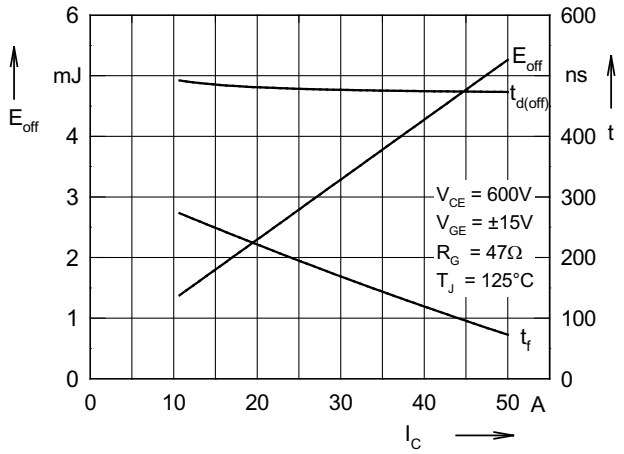

Fig. 8 Typ. turn off energy and switching times versus collector current

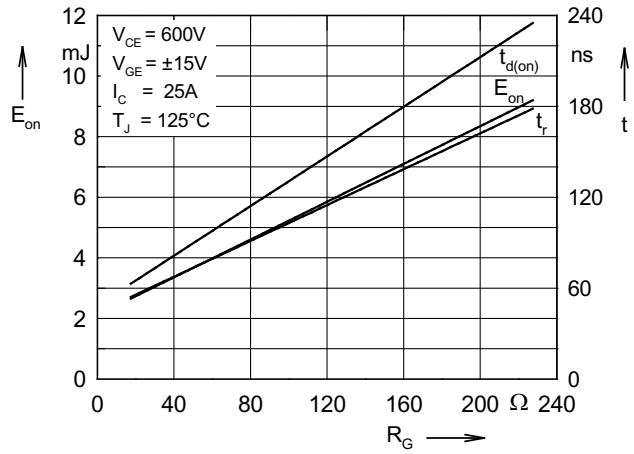

Fig. 9 Typ. turn on energy and switching times versus gate resistor

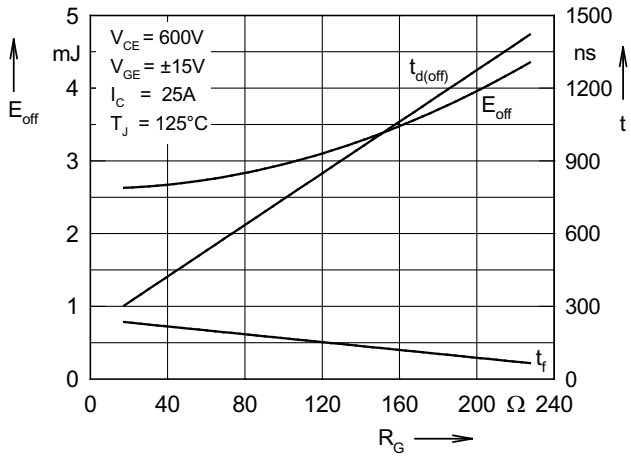

Fig.10 Typ. turn off energy and switching times versus gate resistor

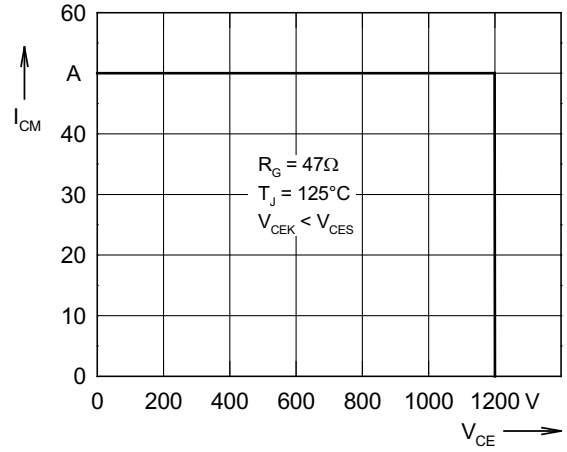

Fig. 11 Reverse biased safe operating area RBSOA

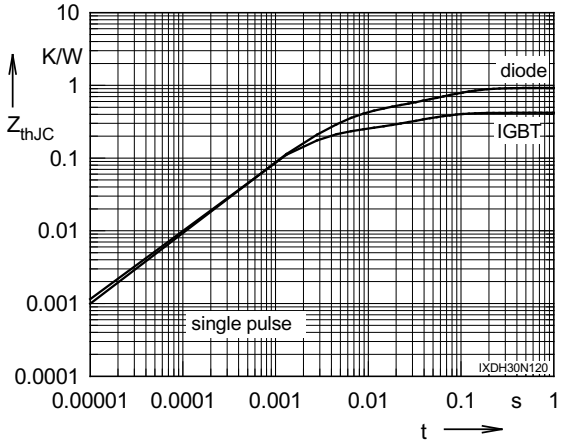

Fig. 12 Typ. transient thermal impedance

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